

## Super FAP-G Series

## N-CHANNEL SILICON POWER MOSFET

### ■ Features

- High speed switching
- No secondary breakdown
- Avalanche-proof
- Low on-resistance
- Low driving power

### ■ Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

### ■ Maximum ratings and characteristic Absolute maximum ratings (Tc=25°C unless otherwise specified)

Item	Symbol	Ratings	Unit	Remarks
Drain-source voltage	V <sub>DS</sub>	120	V	
	V <sub>D SX</sub>	90	V	V <sub>GS</sub> =-30V
Continuous drain current	I <sub>D</sub>	±67	A	
		±6.3	A	T <sub>a</sub> =25°C Note *1
Pulsed drain current	I <sub>D(puls)</sub>	±268	A	
Gate-source voltage	V <sub>GS</sub>	±30	V	
Repetitive or non-repetitive	I <sub>AR</sub>	67	A	Note *2
Non-repetitive Maximum avalanche energy	E <sub>AS</sub>	719.1	mJ	Note *3
Repetitive Maximum avalanche energy		27.0	mJ	Note *4
Maximum drain-source dV/dt	dV <sub>DS</sub> /dt	20	kV/μs	V <sub>DS</sub> ≤ 120V
Peak diode recovery dV/dt	dV/dt	5	kV/μs	Note *5
Maximum power dissipation	P <sub>D</sub>	2.02	W	T <sub>a</sub> =25°C Note *1
		270	W	T <sub>c</sub> =25°C
Operating and storage temperature range	T <sub>ch</sub> T <sub>stg</sub>	+150 -55 to +150	°C	

Note \*1 Surface mounted on 1000mm<sup>2</sup>, t=1.6mm FR-4 PCB (Drain pad area:500mm<sup>2</sup>)

Note \*2 T<sub>ch</sub> ≤ 150°C

Note \*3 Starting T<sub>ch</sub>=25°C, I<sub>AS</sub>=27A, L=1.32mH, V<sub>CC</sub>=48V, R<sub>G</sub>=50Ω  
E<sub>AS</sub> limited by maximum channel temperature and avalanche current.  
See to 'Avalanche Energy' graph.

Note \*4 Repetitive rating : Pulse width limited by maximum channel temperature.  
See to 'Transient Thermal impedance' graph.

Note \*5 I<sub>F</sub> ≤ -I<sub>D</sub>, -di/dt=50A/μs, V<sub>CC</sub> ≤ BV<sub>DSS</sub>, T<sub>ch</sub> ≤ 150°C

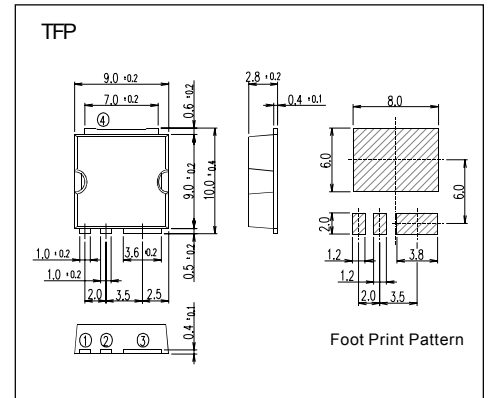
### ● Electrical characteristics (T<sub>c</sub> =25°C unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 250μA V <sub>GS</sub> =0V	120			V
Gate threshold voltage	V <sub>GS(th)</sub>	I <sub>D</sub> = 250μA V <sub>DS</sub> =V <sub>GS</sub>	3.0		5.0	V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =120V V <sub>GS</sub> =0V T <sub>ch</sub> =25°C			25	μA
		V <sub>DS</sub> =96V V <sub>GS</sub> =0V T <sub>ch</sub> =125°C			250	
Gate-source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =±30V V <sub>DS</sub> =0V			100	nA
Drain-source on-state resistance	R <sub>DS(on)</sub>	I <sub>D</sub> =33.5A V <sub>GS</sub> =10V		24.6	30.0	mΩ
Forward transconductance	g <sub>fs</sub>	I <sub>D</sub> =33.5A V <sub>DS</sub> =25V	14	28		S
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> =75V		1880	2820	pF
Output capacitance	C <sub>oss</sub>	V <sub>GS</sub> =0V		360	540	
Reverse transfer capacitance	C <sub>rss</sub>	f=1MHz		30	45	
Turn-on time t <sub>on</sub>	td(on)	V <sub>CC</sub> =48V I <sub>D</sub> =33.5A		20	30	ns
	t <sub>r</sub>	V <sub>GS</sub> =10V		35	53	
Turn-off time t <sub>off</sub>	td(off)	R <sub>GS</sub> =10 Ω		50	75	
	t <sub>f</sub>			23	35	
Total Gate Charge	Q <sub>G</sub>	V <sub>CC</sub> =60V		52	78	nC
Gate-Source Charge	Q <sub>GS</sub>	I <sub>D</sub> =67A		16	24	
Gate-Drain Charge	Q <sub>GD</sub>	V <sub>GS</sub> =10V		18	27	
Diode forward on-voltage	V <sub>SD</sub>	I <sub>F</sub> =67A V <sub>GS</sub> =0V T <sub>ch</sub> =25°C		1.10	1.50	V
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> =67A V <sub>GS</sub> =0V		150		ns
Reverse recovery charge	Q <sub>rr</sub>	-di/dt=100A/μs T <sub>ch</sub> =25°C		0.9		μC

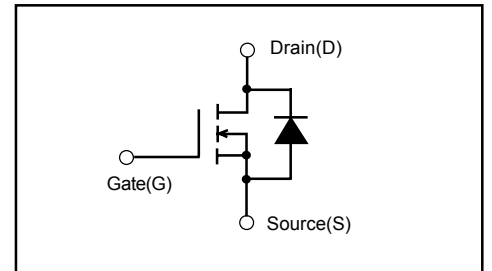
### ● Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	R <sub>th(ch-c)</sub>	channel to case			0.463	°C/W
	R <sub>th(ch-a)</sub>	channel to ambient			87.0	°C/W
	R <sub>th(ch-a)</sub> *1	channel to ambient			52.0	°C/W

### ■ Outline Drawings [mm]



### ■ Equivalent circuit schematic



Characteristics

